

	Type	L #	Hits	Search Text	Time Stamp
1	BRS	L1	36	(RTA or (rapid adj3 thermal adj3 anneal\$3)) same before same after same electrode	2002/10/30 17:37

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TITLE: Semiconductor device with perovskite capacitor and its manufacture method

----- KWIC -----

After the PZT dielectric film 28 is deposited and before or after the upper electrode layer 29 is deposited, an annealing process in an O.sub.2 atmosphere is performed. For example, the annealing process is performed for about 5 seconds at 850.degree. C. in an O.sub.2 atmosphere at one atm. Such an annealing process can be performed by using a rapid thermal anneal (RTA) system. Instead of RTA, an annealing process may be performed by using a resistance heating furnace at 800.degree. C. or higher for 10 minutes or longer, for example, at 800.degree. C. for 30 minutes.